

SPM PROBES & TEST STRUCTURES

MikroMasch® product catalogue

2014



HQ probes

All MikroMasch® SPM Tips upgraded to new HQ (high quality) technology

- · Tip sharpness better than 10 nm
- · High Q-factor and smooth resonance curves
- · Ideal reflectivity from the backside of the cantilever
- · For the old non-HQ price



MikroMasch® SPM Probes & Test Structures

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			,

Improved HQ Probes

All MikroMasch® probes have been upgraded to an improved design, called the HQ Line (High Quality Line).

Since November 2012 all MikroMasch® SPM probes are being manufactured with the new HQ (High Quality) AFM probe technology. The pricing is kept at the same inexpensive level as before.

HQ is the next generation of MikroMasch® probes distinguished by its high quality and high repeatability of characteristics. In particular, the probes have much more consistent reflectivity of uncoated cantilevers, tip radius and quality factor compared to our former standard probes. The HQ probe chips have cut corners that allow them to be used at an angle from the vertical. Described below are some of the main advantages of the improved HO Probes.

RADIUS OF CURVATURE

The radius of curvature measures the sharpness of a particular probe. Typically, the sharper the curvature radius the more fragile a silicon tip is. Conversely, a larger curvature radius provides greater durability, but reduces the benefits of a sharper tip.

Achieving a consistent balance delivers reliable and accurate results. 94% of HQ probes have a radius of curvature between 7 and 10 nm.

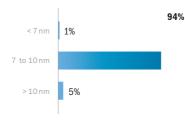
TIP SHAPE FACTOR

A higher value indicates a higher aspect ratio probe. A tighter range of values indicates a more consistent tip shape.

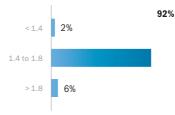
Results of the tip shape factor tests show consistent and close grouping of data. Known tip shape insures accuracy of results. 92% of HO probes have an aspect ratio between 1.4 and 1.8.

RESONANCE FREQUENCY

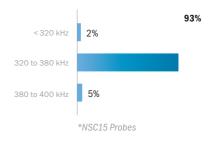
Probes are designed to maintain a tight range of resonance frequencies. Reliability in cantilever specifications ensures dependable measurement results.



*for all standard, uncoated tips



*for all standard, uncoated tips



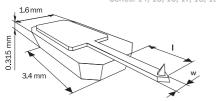
The New HQ Line & Test Structures

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HQ:NSC/CSC 1 - lever

Cantilever material	 n-type silicon
Tip shape	 pyramidal
Tip height	 12 - 18 µm

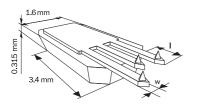
Series: 14, 15, 16, 17, 18, 19



HQ:NSC 3 - lever

Cantilever material n-type silicon	
Tip shape	
Tip height	

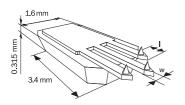
Series: 35, 36



HQ:CSC 3 - lever

Cantilever material	n-type silicon
Tip shape	pyramidal
Tip height	12 - 18 μm

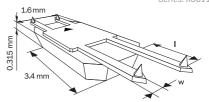
Series: 37, 38



4★ **HQ**: 4 - lever

Cantilever material n-type silicon
Tip shape
Tip height

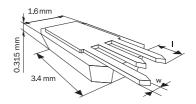
Series: XSC11



HQ: NSC Tipless 3 - lever

Cantilever material								n-type silicon

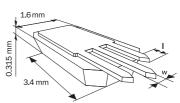
Series: 35,36 Tipless



HQ: CSC Tipless 3 - lever

Cantileve	r material								. n-type silicon	

Series: 37, 38 Tipless



HQ: NSC, CSC & XSC

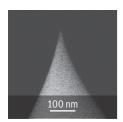








Noncontact (NSC), Contact (CSC) and 4 - Lever (XSC) silicon probes



SEM image of the regular silicon tip $Pyramidal\,silicon\,etched\,probes *\ are\ characterized\ by\ high\ tip\ sharpness\ and\ narrow\ resonance$ peaks, making them very suitable for topography imaging in dynamic AFM modes and compositional mapping. These probes are available in a wide range of resonance frequencies and spring constants.

Tip properties:	Back side coating:
Tip radius ~ 8 nm	AIBS AI30 nm
Tip material silicon	no Alnone
	Cr-Au BS Au 30 nm on Cr 20 nm sublaver

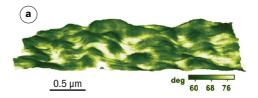
Cantilever	Available	Length	Width	Thickness	Resonance	e Frequency	Force	Constant
Series	Coatings	$l, \pm 5 \; \mu m$	w, $\pm 3~\mu m$	$\pm0.5~\mu m$	kHz			N/m
					(typical)	(range)	(typical)	(range)
■ ▼	▼	•	•	•	▼	•	▼	•
HQ:NSC14	/No AI, /AI BS	125	25	2.1	160	110 - 220	5.0	1.8 - 13
HQ:NSC15	/No AI, /AI BS, /Cr-Au BS	125	30	4.0	325	265 - 410	40	20 - 80
HQ:NSC16	/No AI, /AI BS	225	37.5	7.0	190	170 - 210	45	30 - 70
HQ:CSC17	/No AI, /AI BS	450	50	2.0	13	10 - 17	0.18	0.06 - 0.40
HQ:NSC18	/No AI, /AI BS, /Cr-Au BS	225	27.5	3.0	75	60 - 90	2.8	1.2 - 5.5
HQ:NSC19	/No AI, /AI BS	125	22.5	1.0	65	25 - 120	0.5	0.05 - 2.3
HQ:NSC35								
lever A		110	35	2.0	205	130 - 290	8.9	2.7 - 24
lever B	/No AI, /AI BS, /Cr-Au BS	90	35	2.0	300	185 - 430	16	4.8 - 44
lever C		130	35	2.0	150	95 - 205	5.4	1.7 - 14
HQ:NSC36								
lever A		110	32.5	1.0	90	30 - 160	1.0	0.1 - 4.6
lever B	/No AI, /AI BS, /Cr-Au BS	90	32.5	1.0	130	45 - 240	2	0.2 - 9
lever C		130	32.5	1.0	65	25 - 115	0.6	0.06 - 2.7
-11								
HQ:CSC37								
lever A		250	35	2.0	40	30 - 55	0.8	0.3 - 2
lever B	/No AI, /AI BS	350	35	2.0	20	15 - 30	0.3	0.1 - 0.6
lever C		300	35	2.0	30	20 - 40	0.4	0.1 - 1
HQ:CSC38								
lever A		250	32.5	1.0	20	8 - 32	0.09	0.01 - 0.36
lever B	/No AI, /AI BS	350	32.5	1.0	10	5 - 17	0.03	0.003 - 0.13
lever C		300	32.5	1.0	14	6 - 23	0.05	0.005 - 0.21
4×								
HQ:XSC11								
lever A		500	30	2.7	15	12 - 18	0.2	0.1 - 0.4
lever B	/No Al, /Al BS	210	30	2.7	80	60 - 100	2.7	1.1 - 5.6
lever C	,, , , , , , , , , , , , , , , , ,	150	30	2.7	155	115 - 200	7	3 - 16
lever D		100	50	2.7	350	250 - 465	42	17 - 90

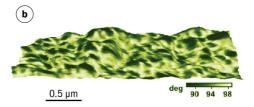
APPLICATION

Phase imaging is among the AFM techniques that can be used to determine nanoscale differences in the properties of a heterogeneous system or of samples with inherent heterogeneity. Phase contrast is dependent on interactions between the tip and the sample, but those interactions are in turn partially dependent on the scan parameters and whether the image is being taken in an attractive or repulsive mode. O'Dea and Burrato used phase imaging to map the proton-conducting domains of a Nafion membrane. They found that the specific interaction forces between the tip and the sample significantly affected the resolution of the proton conducting domains. Imaging in a repulsive regime resulted in an overestimation of the area of the domains and an underestimation in the number of domains. Imaging in an attractive regime resulted in the most accurate phase imaging of the aqueous and fluorocarbon domains of the membrane. When the feedback loop was not optimized or the cantilever was driven above resonance, the phase corresponded with changes in topography rather than changes in the composition of the sample.

In figures (a) and (b) the phase data from repulsive and attractive regimes, respectively, have been overlaid on the corresponding topography image. Features of the phase contrast in the repulsive regime correspond to some features in the topography, while the phase contrast in the attractive regime is independent of the topography. Images were taken with the NSC15/AI BS (now upgraded to HQ:NSC15/AI BS).

(O'Dea, J.R. and Burrato, S.K.; J. Phys. Chem. B 2011, 115, 1014-1020.)







Tipless Cantilevers







Tipless Noncontact (NSC) and Contact (CSC) three-lever silicon probes



SEM image of a tipless silicon cantilever

Probes of the Tipless Series feature 3 tipless cantilevers* with different spring constants and resonance frequencies on one side of the chip. This series replaces the former 12 Series.

Back side coating:	Cr-Au coated
AI BS	Au overall coating 30 nm
no Al no	Cr overall sublaver 20 nm

Cantilever	Available	Length	• , ,			Force	Constant	
Series	Coatings	I, ± 5 μm	w, ± 3 μm	±0.5 μm		Hz		N/m
					(typical)	(range)	(typical)	(range)
Ⅲ ▼	▼	▼	▼	▼	▼	▼	▼	▼
HQ:NSC35/Tiple:	SS							
lever A		110	35	2.0	205	130 - 290	8.9	2.7 - 24
lever B	/No AI, /AI BS, /Cr-Au	90	35	2.0	300	185 - 430	16	4.8 - 44
lever C		130	35	2.0	150	95 - 205	5.4	1.7 - 14
HQ:NSC36/Tipless	3							
lever A		110	32.5	1.0	90	30 - 160	1.0	0.1 - 4.6
lever B	/No AI, /AI BS, /Cr-Au	90	32.5	1.0	130	45 - 240	2	0.2 - 9
lever C		130	32.5	1.0	65	25 - 115	0.6	0.06 - 2.7
ΑΠ								
HQ:CSC37/Tipless	3							
lever A		250	35	2.0	40	30 - 55	0.8	0.3 - 2
lever B	/No AI, /AI BS, /Cr-Au	350	35	2.0	20	15 - 30	0.3	0.1 - 0.6
lever C		300	35	2.0	30	20 - 40	0.4	0.1 - 1
HQ:CSC38/Tipless	S							
lever A		250	32.5	1.0	20	8 - 32	0.09	0.01 - 0.36
lever B	/No AI, /AI BS, /Cr-Au	350	32.5	1.0	10	5 - 17	0.03	0.003 - 0.13
lever C		300	32.5	1.0	14	6 - 23	0.05	0.005 - 0.21

^{*} See specifications on page 5

APPLICATION

Tipless cantilevers can be used for measurements of material properties and interactions. Different objects such as glass spheres or polystyrene particles can also be mounted on tipless cantilevers to make them applicable for AFM-like experiments.



Series HARD







Hardened DLC coated silicon probes



The HARD series silicon etched probe* tips have pyramidal shape. The probes are coated with a hard DLC film. The Back side of the cantilevers is coated with the 30 nm aluminium reflective film.

SEM image of the HARD tip

Cantilever Available Series Coatings		Length Width		Thickness	Resonance Frequency		Force Constant	
Series	ooddiiga	l, ±5 μm	w, ±3 μm	±0.5 μm	kHz			N/m
					(typical)	(range)	(typical)	(range)
■ ▼	▼	•	▼	▼	▼	▼	▼	▼
HQ:NSC14	/Hard/Al BS	125	25	2.1	160	110 - 220	5.0	1.8 - 13
HQ:NSC15	/Hard/Al BS	125	30	4.0	325	265 - 410	40	20 - 80
HQ:NSC16	/Hard/Al BS	225	37.5	7.0	190	170 - 210	45	30 - 70
HQ:CSC17	/Hard/Al BS	450	50	2.0	13	10 - 17	0.18	0.06 - 0.40
HQ:NSC18	/Hard/Al BS	225	27.5	27.5	75	60 - 90	2.8	1.2 - 5.50
THI .								
HQ:NSC35								
lever A	/Hard/Al BS	110	35	2.0	205	130 - 290	8.9	2.7 - 24
lever B		90	35	2.0	300	185 - 430	16	4.8 - 44
lever C		130	35	2.0	150	95 - 205	5.4	1.7 - 14
HQ:NSC36								
lever A	/Hard/Al BS	110	32.5	1.0	90	30 - 160	1.0	0.1 - 4.6
lever B		90	32.5	1.0	130	45 - 240	2	0.2 - 9
lever C		130	32.5	1.0	65	25 - 115	0.6	0.06 - 2.7
4x								
HQ:XSC11								
lever A	/Hard/Al BS	500	30	2.7	15	12 - 18	0.2	0.1 - 0.4
lever B	/ Halu/ Al Bo	210	30	2.7	80	60 - 100	2.7	1.1 - 5.6
lever C		150	30	2.7	155	115 - 200	7	3 - 16
lever D		100	50	2.7	350	250 - 465	42	17 - 90

* See specifications on page 5

APPLICATION

The wear-resistant diamond-like carbon (DLC) coating increases tip durability and lifetime. DLC coated probes are useful for scanning large areas and very hard materials.

PART NUMBER		N, X	type
	HQ: * SC * / Hard / Al BS / *-	15, 50	quantity
		11, 14, 15, 16, 17, 18, 35, 36	series

DPER





High Resolution Conductive silicon probes



SEM image of the DPER silicontip

DPER probes* are made by depositing a thin platinum coating on silicon tips. While the thickness of the coating on a flat cantilever surface is about 15 nm, there is only a 10 nm increase in the tip dimensions compared to bare silicon probes. These probes are recommended for electrical applications requiring higher resolution.

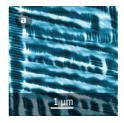
Cantilever Series	Length I, ± 5 µm	Width w, ± 3 μm	Thickness ±0.5 µm	Resonance Frequency			Constant N/m
				(typical)	(range)	(typical)	(range)
4x	▼	•	•	•	▼	•	•
HQ:DPER-XSC11							
lever A	500	30	2.7	15	12 - 18	0.2	0.1 - 0.4
lever B	210	30	2.7	80	60 - 100	2.7	1.1 - 5.6
lever C	150	30	2.7	155	115 - 200	7	3 - 16
lever D	100	50	2.7	350	250 - 465	42	17 - 90

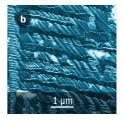
^{*} See specifications on page 5

APPLICATION

Topography (a) and in-plane piezoelectric force response (b) images of an approximately 80 nm thick $BiFeO_3$ film grown on a LaAlO $_3$ substrate taken with a DPER18 probe (now replaced by H0:DPE-XSC11).

Image courtesy of Zuhuang Chen, Nanyang Technological University.





PART NUMBER

HQ: DPER - XSC11 / * -

15, 50, 100

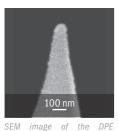
quantity

DPE





Low Noise Conductive silicon probes



silicon tip

topography images is possible when using DPE probes due to the increased tip radius.

The DPE probes* feature silicon tips and a special structure of conductive layers, which provides a more stable electrical signal and less noise. However, some reduction in resolution for

Pt coated resulting tip radius. . . . < 40 nm
Pt overall coating. 50 nm

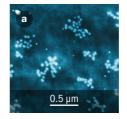
Cantilever Series	Length I, ±5 μm	Width w, ±3 μm	Thickness ± 0.5 μm	Resonance Frequency kHz (typical) (range)		Force Constant N/m (typical) (range)	
4x ■ ▼	▼	▼	•	▼	▼	▼	▼
HQ:DPE-XSC11							
lever A	500	30	2.7	15	12 - 18	0.2	0.1 - 0.4
lever B	210	30	2.7	80	60 - 100	2.7	1.1 - 5.6
lever C	150	30	2.7	155	115 - 200	7	3 - 16
lever D	100	50	2.7	350	250 - 465	42	17 - 90

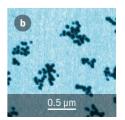
^{*} See specifications on page 5

APPLICATION

DPE probe topography (a) and surface potential (b) images of a fluoroalkane ($F_{12}H_{20}$) on a Silicon substrate.

Image was taken using single-pass KFM with an Agilent 5500 by S. Magonov.





HQ: DPE - XSC11 / * -

15, 50, 100

quantity

Pt and Cr-Au Coated



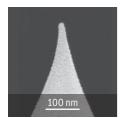


Force Constant





Conductive Noncontact (NSC), Contact (CSC) and 4 - Lever (XSC) silicon probes



SEM image of the conducting silicon tip

Cantilover

Pyramidal silicon etched probes* with conductive platinum or gold coatings are suitable for a wide range of electrical applications of AFM. Gold and platinum coatings are inert, which makes these probes applicable for many experiments in biology and chemistry.

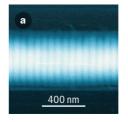
Pt coated resulting tip radius < 30 nm	Cr-Au coated resulting tip radius	< 35 nm
Pt overall coating 30 nm	Au overall coating	. 30 nm
	Cr overall sublayer	. 20 nm

Cantilever	Available	Length	Width	Thickness	Resonance Frequency		Force Constant	
Series	Coatings	$l, \pm 5 \; \mu m$	w, $\pm 3 \mu m$	$\pm0.5~\mu m$	kHz			N/m
					(typical)	(range)	(typical)	(range)
▼	▼	▼	▼	•	▼	▼	▼	•
HQ:NSC14	/Cr-Au, /Pt	125	25	2.1	160	110 - 220	5.0	1.8 - 13
HQ:NSC15	/Cr-Au, /Pt	125	30	4.0	325	265 - 410	40	20 - 80
HQ:NSC16	/Cr-Au,	225	37.5	7.0	190	170 - 210	45	30 - 70
HQ:CSC17	/Cr-Au, /Pt	450	50	2.0	13	10 - 17	0.18	0.06 - 0.4
HQ:NSC18	/Cr-Au, /Pt	225	27.5	3.0	75	60 - 90	2.8	1.2 - 5.5
HQ:NSC19	/Cr-Au	125	22.5	1.0	65	25 - 120	0.5	0.05 - 2.3
HQ:NSC35								
lever A		110	35	2.0	205	130 - 290	8.9	2.7 - 24
lever B	/Cr-Au, /Pt	90	35	2.0	300	185 - 430	16	4.8 - 44
lever C		130	35	2.0	150	95 - 205	5.4	1.7 - 14
HQ:NSC36								
lever A		110	32.5	1.0	90	30 - 160	1.0	0.1 - 4.6
lever B	/Cr-Au, /Pt	90	32.5	1.0	130	45 - 240	2	0.2 - 9
lever C		130	32.5	1.0	65	25 - 115	0.6	0.06 - 2.
1								
HQ:CSC37								
lever A		250	35	2.0	40	30 - 55	0.8	0.3 - 2
lever B	/Cr-Au, /Pt	350	35	2.0	20	15 - 30	0.3	0.1 - 0.6
lever C		300	35	2.0	30	20 - 40	0.4	0.1 - 1
HQ:CSC38								
lever A		250	32.5	1.0	20	8 - 32	0.09	0.01 - 0.3
lever B	/Cr-Au	350	32.5	1.0	10	5 - 17	0.03	0.003 - 0.
lever C		300	32.5	1.0	14	6 - 23	0.05	0.005 - 0.
]								
HQ:XSC11								
lever A		500	30	2.7	15	12 - 18	0.2	0.1 - 0.4
lever B	/Pt	210	30	2.7	80	60 - 100	2.7	1.1 - 5.6
lever C	/ F t	150	30	2.7	155	115 - 200	7	3 - 16
lever D		100	50	2.7	350	250 - 465	42	17 - 90

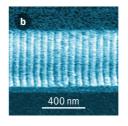
APPLICATION

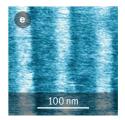
AFM is capable of mapping different electric properties of materials to topography images. These data can be used for analysis of the structure and composition of heterogeneous samples as well as for quantitative characterization of individual grains or defects on the surface. Electric properties of a sample can be mapped using probes with conducting coatings, when AC or DC bias is applied between the tip and the sample. Contact mode or two-pass operation techniques can be used for this purpose.

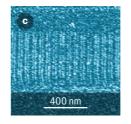
Although traditional piezoelectric and ferroelectric materials are often the samples studied using piezoresponse force microscopy, Minary-Jolandan and Yu showed that the electromechanical properties of collagen fibrils can also be investigated with PFM. They found via high resolution PFM with a Pt coated CSC17 probe (now upgraded to HO:CSC17/ Pt) that collagen fibrils have piezoelectrically heterogeneous gap and overlap regions. The gap regions exhibit little to no piezoelectricity, while the overlap regions show piezoelectricity. Images (a) and (d) show the topography of the collagen fibril, while (b) and (e) show the PFM amplitude. (c) and (f) are the 2ω signal measured to rule out any electrostatic interference with the PFM signal. The Pt only coating on the CSC17 probe (now upgraded to HQ:CSC17/Pt) allowed for the resolution of features ~30 nm. (Minary-Jolandan, M. and Yu, M.-F.; ACS Nano 2009, 3, 1859-1863.)

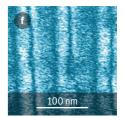












PART NUMBER HO		N, C, X	type
		11, 14, 15, 16, 17, 18, 19, 35, 36, 37, 38	series
	HQ: * SC * / * / * ——	15, 50, 100	quantity
		/Cr-Au, /Pt	coating

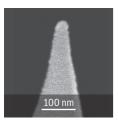
Co-Cr Coated







Magnetic Noncontact (NSC) silicon probes



SEM image of the magnetic silicon tip

Two HQ:NSC probe* models are available with a special coating for Magnetic Force Microscopy. The coating consists of a 60 nm cobalt layer on the tip side and is protected from oxidation with a 20 nm chromium film. The cantilever parameters are optimized for stable measurements of topography and magnetic properties.

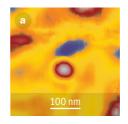
Co-Cr coated tip < 60 nm	Back side Al coating 30 nm
Co tip side coating 60 nm	
Cr tip side coating 20 nm	Coercivity 300-400 Oe

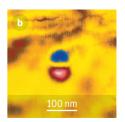
Cantilever Series	Available Coatings	Length I, ± 5 μm	Width w, ± 3 μm	Thickness ±0.5 μm		e Frequency Hz (range)		Constant N/m (range)
■ ▼	▼	▼	▼	▼	▼	▼	▼	▼
HQ:NSC18	/Co-Cr/AI BS	225	27.5	3.0	75	60 - 90	2.8	1.2 - 5.5
1.1								
HQ:NSC36								
lever A		110	32.5	1.0	90	30 - 160	1.0	0.1 - 4.6
lever B	/Co-Cr/Al BS	90	32.5	1.0	130	45 - 240	2	0.2 - 9
lever C		130	32.5	1.0	65	25 - 115	0.6	0.06 - 2.7

^{*} See specifications on page 5

APPLICATION

Topography (a) and magnetic (b) images of a Co mono domain particle obtained in Lift Mode using a NSC36 series cantilever with Co-Cr coating (now upgraded to HQ:NSC36/Co-Cr/AI BS). Image courtesy of Prof. V. Shevyakov, MIET.





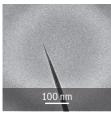
DADT NUMBER	HO. NCC - /Co. C. / ALDC / -	18,36	series
PART NUMBER	HQ: NSC * / Co-Cr / Al BS / *	15, 50	quantity

Hi'Res-C

TIP



High Resolution silicon probes



SEM image of the Hi'Res-C

The Hi'Res-C probes* suffer less contamination than silicon probes and are capable of obtaining many high-resolution scans, although they do require special care in use. Due to the small tip curvature radius, the tip-sample attraction force is minimized.

Advantages of Hi'Res-C are noticeable when scanning small areas (< 250 nm) and flat samples ($R_a < 20$ nm). On larger images, the resolution is similar to that of General Purpose probes.

Spike radius	Overall coating:
Spike height	Au overall coating 30 nm
Spike material diamond-like	Cr overall sublayer 20 nm
	The coating does not cover the spike!

Cantilever Series	Available Coatings	Length I, ± 5 μm	Width w, ±3 μm	Thickness ±0.5 μm		e Frequency (Hz (range)		Constant N/m (range)
■ ▼	▼	•	•	•	•	▼	•	▼
Hi'Res-C14	/Cr-Au	125	25	2.1	160	110 - 220	5.0	1.8 - 13
Hi'Res-C15	/Cr-Au	125	30	4.0	325	265 - 410	40	20 - 80
Hi'Res-C19	/Cr-Au	125	22.5	1.0	65	25 - 120	0.5	0.05 - 2.3

* See specifications on page 5

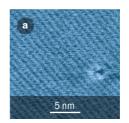
APPLICATION

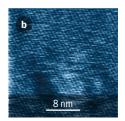
PAR

The advantages of the Hi'Res-C probes are noticeable on scans less than 250 nm in size. The tip radius of 1 nm allows high resolution imaging of nanometer-sized objects like single molecules, ultrathin films, and porous materials in air.

(a) Height image of polydiacetylene crystal obtained with Dimension 5000 SPM microscope and Hi'Res-C probe. Scan size 15 nm. A single defect in the molecular lattice of PDA crystal is visible. (b) Height image of PDA crystal obtained with Agilent 5500 SPM microscope and Hi'Res-C14 probe. Scan size 23 nm. Molecular lattice of PDA is observed only.

Images courtesy of Dr. S. Magonov, Agilent Technologies.

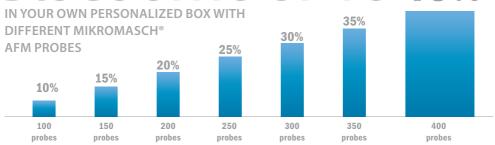




RT NUMBER	H:/Dara Car / Car Asa / a	, _	14, 15, 19	series
	Hi'Res - C * / Cr-Au /	* / Cr-Au / * —	5, 15	quantity



DISCOUNTS UP TO 40%



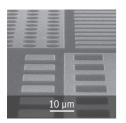
Mix and Match enables you to create a custom MikroMasch® AFM probes box with quantities of 100, 150, 200, 250, 300, 350 or 400 pcs. inside where you can mix different MikroMasch® AFM probe types in units of 50 pcs.

The more units of 50 AFM probes you order, the higher your discount will be from the 50 probes list prices of each variety ordered:



YOU CAN CREATE YOUR OWN MIKROMASCH® BOX USING THE FORM ON OUR WEBSITE. WE WILL SHIP YOUR PERSONAL MIX AND MATCH BOX WITHIN 10 BUSINESS DAYS.

TGXYZ Series



SEM image of a TGXYZ02 grating

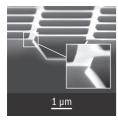
Calibration gratings from the TGXYZ series are arrays of different structures comprising rectangular silicon dioxide steps on a silicon wafer. The small square in the center with dimensions $500~\mu m$ by $500~\mu m$ includes circular pillars and holes, as well as lines in the X- and Y-direction with a pitch of $5~\mu m$. The large square with dimensions 1 mm by 1 mm contains square pillars and holes with a pitch of $10~\mu m$.

Active area			1x	1 mm		
Chip dimens	sions		5x5x0.	3 mm		
Part number	Step height*	Height accuracy	Pitch	Pitch accuracy	step height*	71 /
•	▼	•	▼	▼	del /	$\overline{}$
TGXYZ01	20 nm	2%	5 and 10 µm	0.1 μm		
TGXYZ02	100 nm	3%	5 and 10 μm	0 .1 μm	pitch*	
TGXYZ03	500 nm	3%	5 and 10 µm	0.1 μm	- piteri	
step height, s		el of the indiv	reference only. idual grating bo			

APPLICATION

The TGXYZ calibration gratings are intended for vertical and lateral calibration of SPM scanners. The vertical non-linearity can be compensated for by using several calibration gratings with different nominal step heights.

TGX Series



SEM image of a TGX01 grating

The silicon calibration grating TGX is an array of square holes with sharp undercut edges formed by the (110) crystallographic planes of silicon. The typical radius of the edges is less than 5 nm.

Part number	
Active area	height edge

APPLICATION

TGX calibration gratings are intended for determination of the tip aspect ratio and for lateral calibration of SPM scanners. The gratings can also be used for detection of lateral non-linearity, hysteresis, creep, and cross-coupling effects.

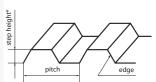
TGF11 Series



SEM image of a TGF11 grating

The TGF calibration gratings feature one-dimensional arrays of trapezoidal steps etched into a silicon substrate. The sidewalls of the structures are very smooth and planar surfaces with well-defined orientation formed by the (111) crystallographic planes in monocrystalline silicon. The sidewalls and the horizontal top surfaces form an angle of 54°74′.

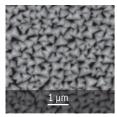
Part number	
Active area .3 x 3 mm Chip dimensions .5 x 5 x 0.3 mm Pitch .10 μm Pitch accuracy 0.1 μm Step height* 1.75 μm	pitch
The step height value is given for information only, not for vertical	



APPLICATION

TGF11 grating can be used for the assessment of scanner nonlinearity in the vertical direction. Direct calibration of the lateral force can be obtained by analyzing the contact response measured on the flat and sloped facets. This can be done for the calibration of conventional Si probes or cantilevers with an attached colloidal particle with any radius of curvature up to 2 µm.

PA Series



SEM image of a PA01 structure Scan size 1 µm

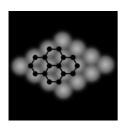
Sample for characterization of tip shape with hard sharp pyramidal nanostructures. The structures are covered by a highly wear-resistant layer.

Part number	. PA01
Pyramid base50 -	100 nm
Pyramid height	150 nm
Smallest edge radii	< 5 nm
Active area	x 5 mm
Chip dimensions	0.3 mm

APPLICATION

The exact shape of the scanning probe tip is very important for obtaining AFM images of high quality and accuracy. As new AFM tips with nanometer radii of curvature become widespread, periodic structures that have surface features of similar or greater sharpness should be used to estimate the parameters of the tip.

HOPG



Typical STM image of HOPG with superimposed graphene structure

Highly ordered pyrolytic graphite (HOPG) is a lamellar material and consists of stacked planes. Carbon atoms within a single plane interact more strongly than with those in adjacent planes. Each atom within a plane has three nearest neighbors, resulting in a honeycomb-like structure. This two-dimensional single-atom thick plane is called graphene.

Part number:			
HOPG/ZYA/DS/1	-1		10 x 10 x 1 mm, 1 chip
HOPG/ZYA/DS/2	-1		10 x 10 x 2 mm, 1 chip
HOPG/ZYB/DS/1	-1		10 x 10 x 1 mm, 1 chip
HOPG/ZYH/DS/1	-1		10 x 10 x 1 mm, 1 chip
HOPG/ZYH/DS/2	-1		10 x 10 x 2 mm, 1 chip
HOPG/ZYH/DS/1	-5		10 x 10 x 1 mm, 5 chips
HOPG/ZYH/DS/2	-5		10 x 10 x 2 mm, 5 chips
Density Thermal conduct			2.266 g/cm ³
thermal conducti	vity parallel (002)		
thermal conductiv	vity perpendicula	r (002)	
			2.1 ± 0.1 x 10 ⁶ [(Ω ·m) ⁻¹]
electrical conduc	tivity perpendicul	ar (002)	5 x 10^2 [(Ω ·m) ⁻¹]
There are several	grades of single -	or double sided HC	PG with thickness 1 mm or more:
	ZYA Grades	ZYB Grades	ZYH Grades
Mosaic spread	0.4°±0.1°	0.8°±0.2°	3.5°± 1.5°

APPLICATION

HOPG terminated with a graphene layer can serve as an ideal atomically flat surface to be used as a substrate or standard for SPM investigations. This is also an easily "cleavable" material with a smooth surface, which is vital for SPM measurements that require a uniform, flat and clean substrate.



PLEASE NOTE

The TGXYZ, TGX, TGF11, and PA Series Calibration Gratings are available either mounted on a round metal plate with Ø12mm or unmounted. For ordering information visit www.spmtips.com

RECOMMENDATIONS FOR SPECIFIC APPLICATIONS

	Probe Type	Characteristics	k, N/m	f _a , kHz	Tip Material, Coating	P nm
		- Onaractoristics	A, 14/111	, KIIZ		R _{tip} , nm
Materials characterization	HQ:NSC18	Force modulation	~2.8	~75	Silicon, Al or no Al Back side coating	~8
	HQ:NSC14	Phase imaging	~5.0	~150	Silicon, Al or no Al Back side coating	~8
General topology imaging	HQ:NSC17	Contact imaging	~0.18	~13	Silicon, Al or no Al Back side coating	~8
	HQ:NSC15	Intermittent/non-contact Imaging	~40	~325	Silicon, Al or no Al Back side coating	~8
	HQ:NSC14	Intermittent contact imaging	~5.0	~150	Silicon, Al or no Al Back side coating	~8
Topology imaging for life science	HQ:NSC14	Intermittent contact imaging	~5.0	~150	Silicon, Al or no Al Back side coating	~8
	HQ:NSC18/ Cr-Au BS	Intermittent contact imaging in fluid	~2.8	~75	Silicon, Au Back side coating	~8
	HQ:NSC18/Cr-Au BS	Contact imaging in fluid	~2.8	~75	Silicon, Au Back side coating	~8
	HQ:CSC17	Contact imaging	~0.18	~13	Silicon, Al or no Al Back side coating	~8
	HQ:CSC38 (three lever)	Contact imaging	~0.09 ~0.03 ~0.05	~20 ~10 ~14	Silicon, Al or no Al Back side coating	~8
	Hi'Res-C14/Cr-Au	High resolution Imaging	~5.0	~160	Carbon spike, Al Back side coating	~1
	HQ:NSC36 (three lever)	Intermittent contact imaging	~1.0 ~2.0 ~0.6	~90 ~130 ~65	Silicon, Al or no Al Back side coating	~8
Probes for mechanical property	HQ:NSC14/Hard	Specially coated for durability	~5.0	~160	DLC coating, Al Back side coating	<20
measurements in Life Science	HQ:NSC18	Force modulation	~2.8	~75	Silicon, Al or no Al Back side coating	~8
	HQ:CSC17/Cr-Au	Chemical inertness, functionalization	~0.18	~13	Cr-Au coating on both sides	<35
Probes for high resolution imaging	Hi'Res-C14/Cr-Au	Nanometer-sized objects like single molecules, ultrathin films, and porous materials in air	~5.0	~160	Carbon spike, Cr-Au coating on both sides (spike not coated)	~1
Electrical applications in	HQ:DPER/XS11, Cantilever A	High resolution	~0.2	~15	Pt coating on both sides	<20
vacuum	HQ:DPE/XSC11, Cantilever A	High sensitivity, low wear	~0.2	~15	Pt coating on both sides	<40

k – Force constant; f_0 – Resonance frequency

	Probe Type	Characteristics			Tip Material, Coating	
Electrical applications for	HQ:DPER/XSC11, Cantilever C	High resolution	~7	~155	Pt coating on both sides	<20
PFM, TUNA, SCM, SSRM	HQ:DPE/XSC11, Cantilever C	Dynamic/contact electrical mode, high sensitivity, low wear	~7	~155	Pt coating on both sides	<40
	HQ:CSC17/Cr-Au	Chemical inertness, functionalization	~0.15	~12	Cr-Au coating on both sides	<35
	HQ:NSC18/Pt	Dynamic/contact electrical mode	~2.8	~75	Pt coating on both sides	<30
Electrical applications for	HQ:DPER/XSC11, Cantilever C	High resolution	~7	~155	Pt coating on both sides	<20
EFM, SKPM, Voltage Modulation, Scan- ning Impedance Microscopy, SGM	HQ:DPE/XSC11, Cantilever C	Dynamic/contact electrical mode, high sensitivity, low wear	~7	~155	Pt coating on both sides	<40
	HQ:NSC14/Pt	General stability in conductive modes	~7	~155	Pt coating on both sides	<30
	HQ: NSC14/Cr-Au	Chemical inertness, functionalization	~7	~155	Cr-Au coating on both sides	<35
	HQ:DPER/XSC11, Cantilever B	High resolution	~2.7	~80	Pt coating on both sides	<20
	HQ:DPE/XSC11, Cantilever B	High sensitivity, low wear	~2.7	~80	Pt coating on both sides	<40
	HQ:NSC18/Pt	General stability in conductive modes	~2.8	~75	Pt coating on both sides	<30
	HQ:NSC18/Cr-Au	Chemical inertness, functionalization	~2.8	~75	Cr-Au coating on both sides	<35
Magnetic force microscopy	HQ:NSC18/Co-Cr/ AI BS	Magnetic coating	~2.8	~75	Co-Cr coating, AI Back side coating	<90

k – Force constant; $f_{_{0}}$ – Resonance frequency

Notes # | Get a free poster #2.....



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